



Semiconductor Device and a Method of Creating the Same Utilizing Metal Induced  
Crystallization While Suppressing Partial Solid Phase Crystallization  
Serial No.: 09/696,813  
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1/6

Fig. 1A

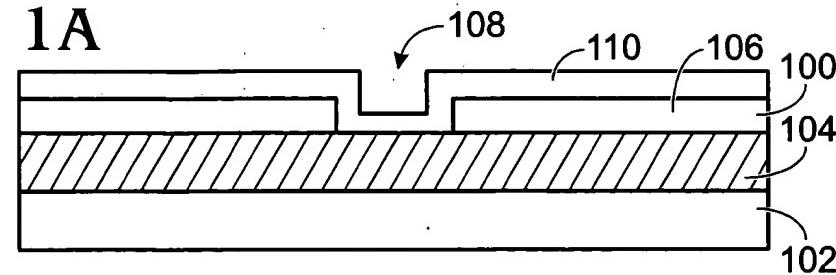


Fig. 1B

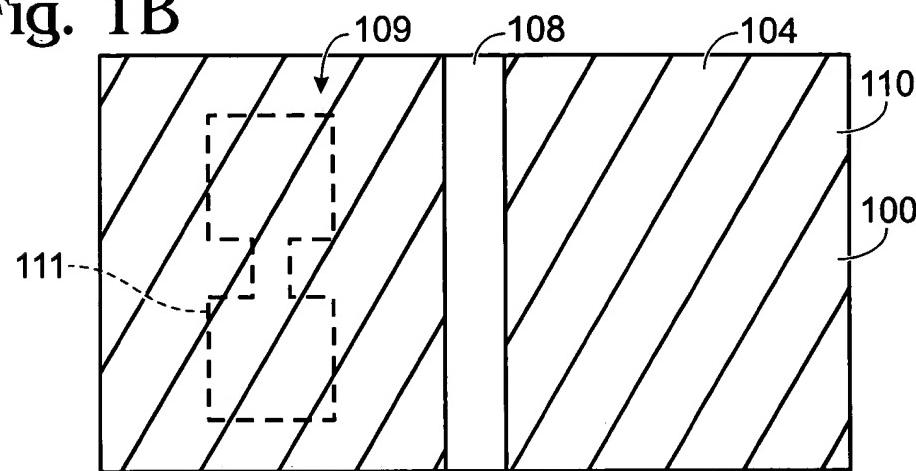


Fig. 1C

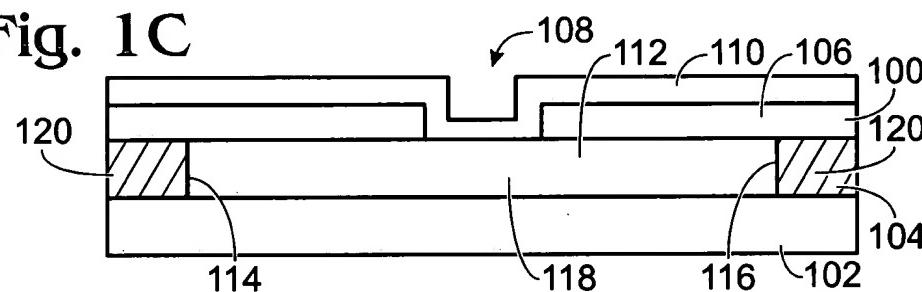


Fig. 1D

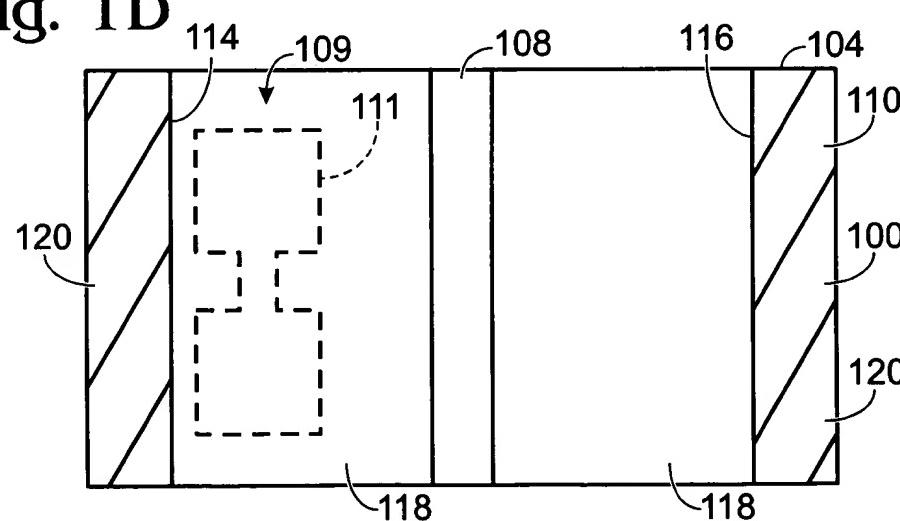


Fig. 2A

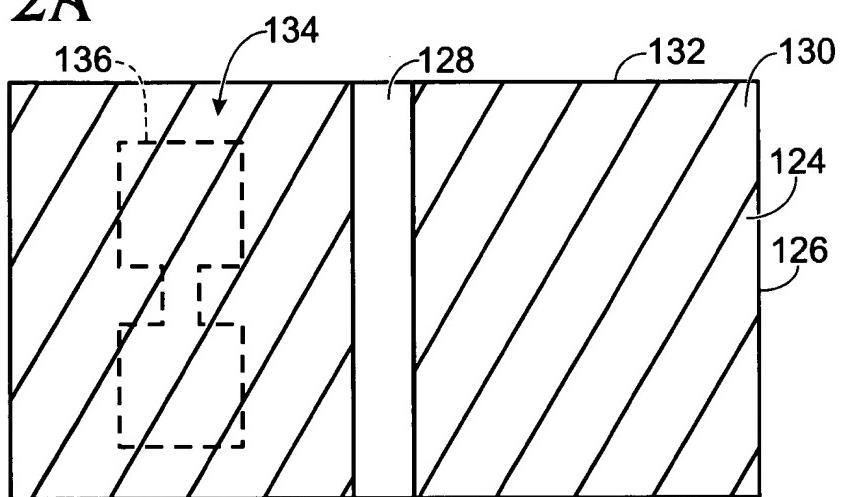


Fig. 2B

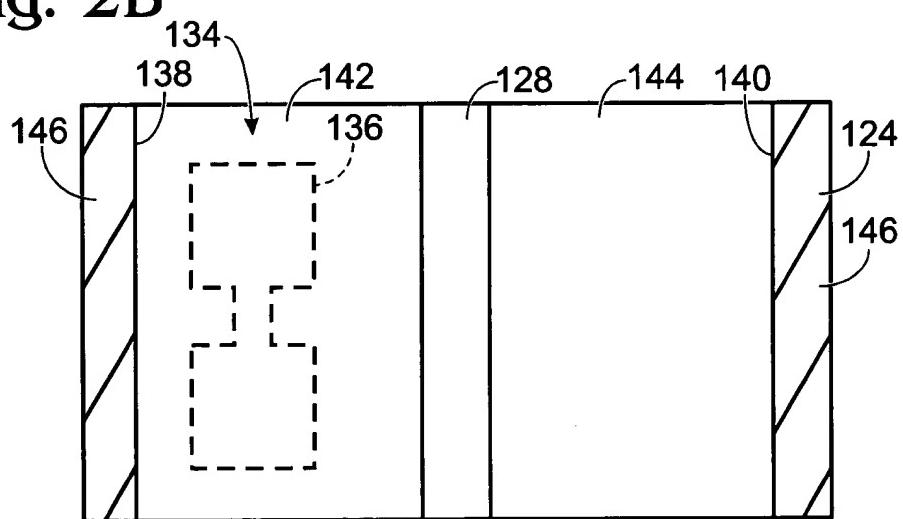


Fig. 2C

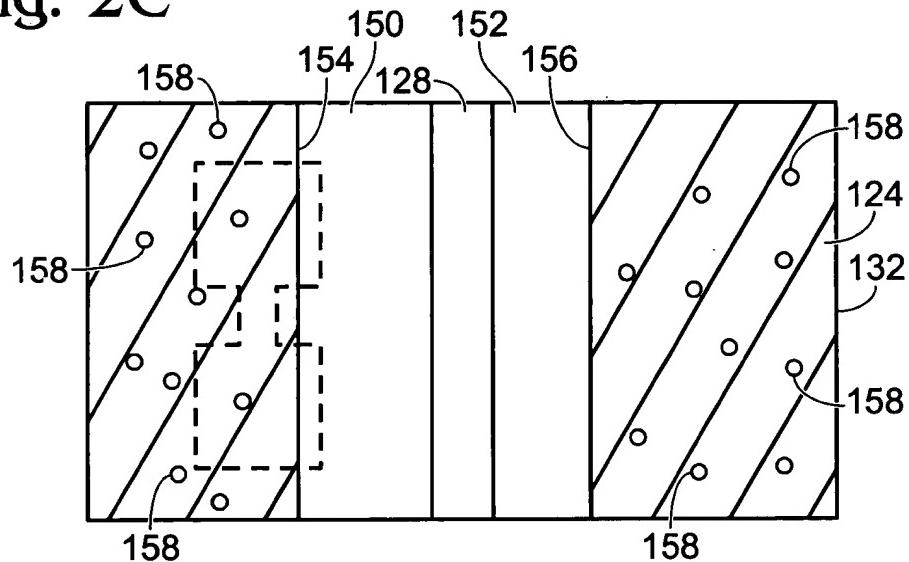
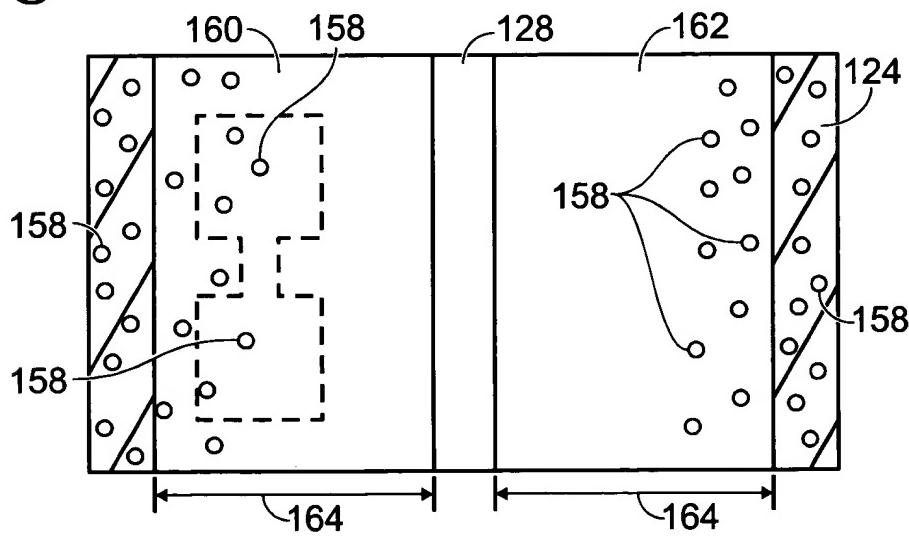
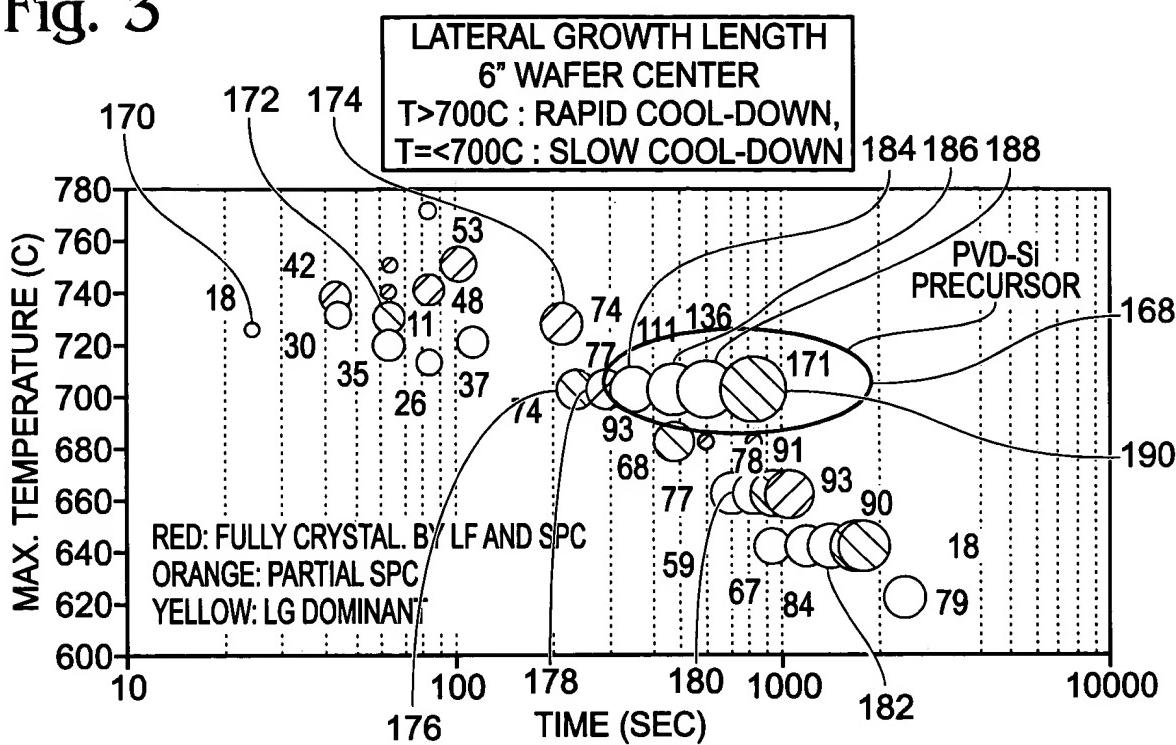


Fig. 2D



**Fig. 3**



**Fig. 4**

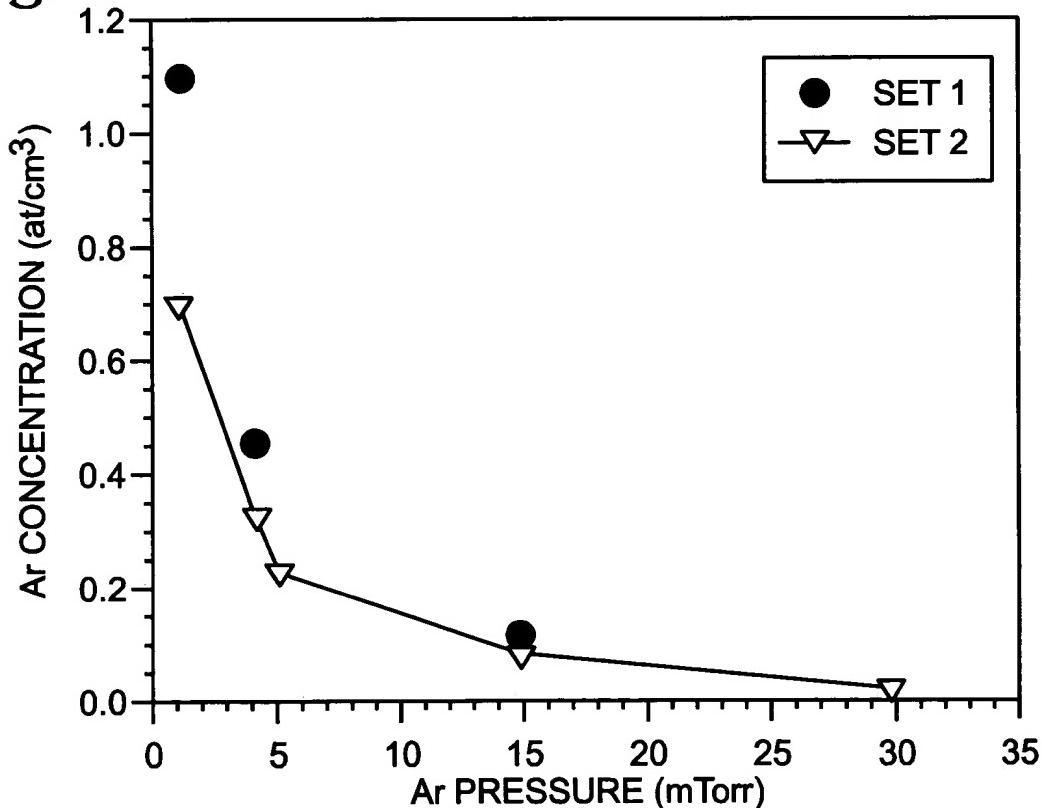


Fig. 5

POWER (kW)	PRESSURE (mTorr)	SPUTTERING GAS	Ar CONTENT (at/cm <sup>3</sup> )
8	14-16	PURE He	<2X10 <sup>18</sup>
		He/(3.8%)Ar	2-5X10 <sup>18</sup>
		He/(10%)Ar	4-7X10 <sup>18</sup>
		PURE Ar	6X10 <sup>19</sup>
8	5-6	PURE Ar	2X10 <sup>20</sup>

Fig. 6

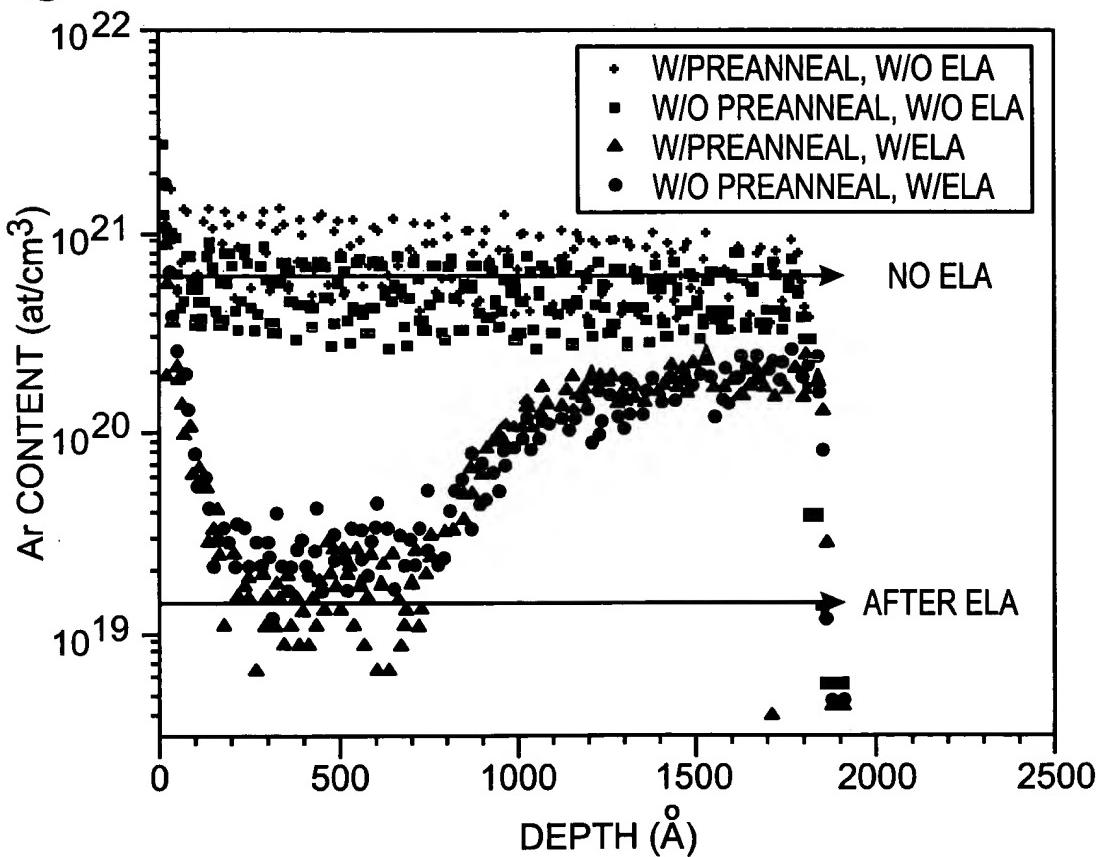


Fig. 7

